

directly exposing said conductive material to a selection consisting of diborane, phosphine, methylsilane, hexamethyldisilane, hexamethyldisilazane, HCL, boron trichloride, and combinations thereof to reduce the ability of the conductive material to associate with oxygen prior to forming another conductive material on the conductive material.

76. (Amended) A method of passivating a conductive layer, comprising:
providing a tungsten nitride layer;
providing a polysilicon layer on the tungsten nitride layer; and
exposing the tungsten nitride layer to a selection consisting of diborane, phosphine, methylsilane, hexamethyldisilane, hexamethyldisilazane, HCL, boron trichloride, and combinations thereof to passivate the tungsten nitride layer prior to formation of the polysilicon layer on the tungsten nitride layer.

77. (Amended) The method in claim 76, wherein exposing the tungsten nitride layer causes a reduction in an ability of the tungsten nitride layer to associate with oxygen.

81. (Amended) A method of passivating a conductive layer, comprising:
providing a first conductive plug;
providing a first conductive layer on the plug;
exposing the first conductive layer to a selection consisting of diborane, phosphine, methylsilane, hexamethyldisilane, hexamethyldisilazane, HCL, boron trichloride, and combinations thereof to passivate the first conductive layer; and
after exposing the first conductive layer, forming a second conductive layer on the first conductive layer.

85. (Amended) The method of claim 81 wherein exposing the first conductive layer reduces an ability of the first conductive layer to associate with oxygen.